



Schottky Barrier Diode

Features

1. Small surface mounting type
2. High reliability
3. Low leakage current
4. low forward voltage drop
5. Low capacitance



Applications

Diode for low currents with a low supply voltage

Small battery charger

HF-Detector

Protection circuit

DC/DC converter for notebooks

Protection circuit

Absolute Maximum Ratings

T_j=25°C

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage		BAS81	V _{RRM}	40	V
		BAS82	V _{RRM}	50	V
		BAS83	V _{RRM}	60	V
Repetitive peak forward current			I _{FRM}	150	mA
Peak forward surge current	t _p =1 s		I _{FSM}	500	mA
Forward current			I _F	30	mA
Junction temperature			T _j	125	°C
Storage temperature range			T _{stg}	-65~+150	°C

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

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Electrical Characteristics

$T_j=25 \text{ } ^\circ\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=0.1\text{mA}$		V_F			0.33	V
	$I_F=1\text{mA}$		V_F			0.41	V
	$I_F=15\text{mA}$		V_F			1	V
Reverse current	$V_R=40\text{V}$	BAS81	I_R			0.2	μA
	$V_R=50\text{V}$	BAS82	I_R			0.2	μA
	$V_R=60\text{V}$	BAS83	I_R			0.2	μA
Diode capacitance	$V_R=1\text{V}, f=1\text{MHz}$		C_D			1.6	pF

Characteristics ($T_j=25$

$^\circ\text{C}$ unless otherwise specified)

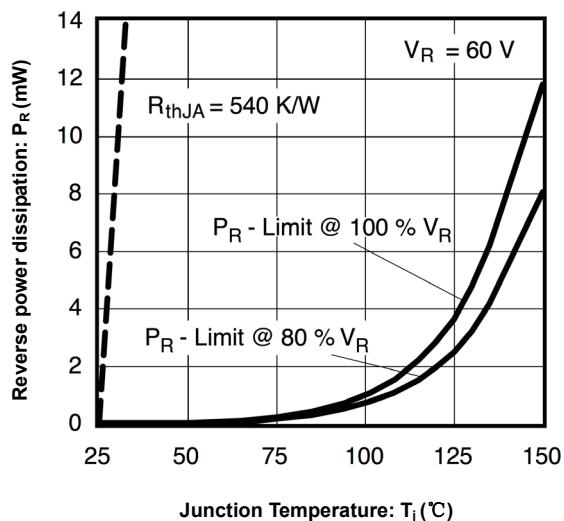


Figure 1. Max. reverse power dissipation
vs. junction temperature

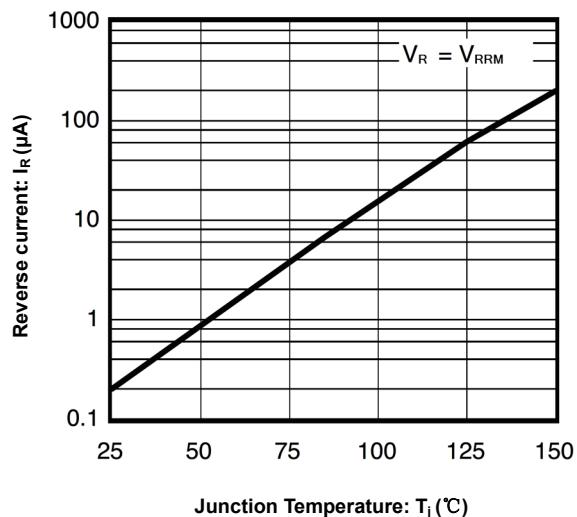


Figure 2. Reverse current vs. junction temperature

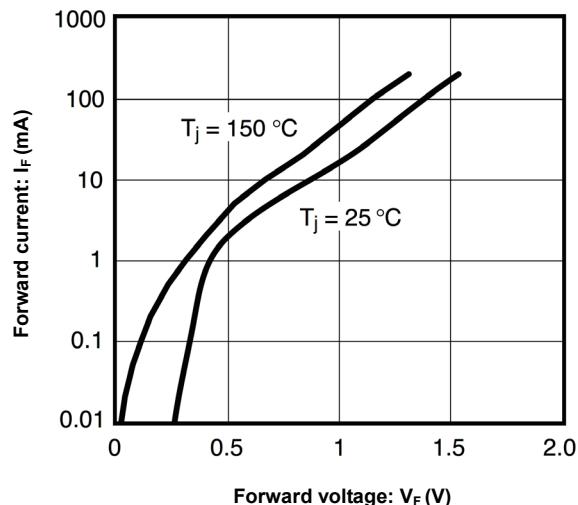


Figure 3. Forward current vs. forward voltage

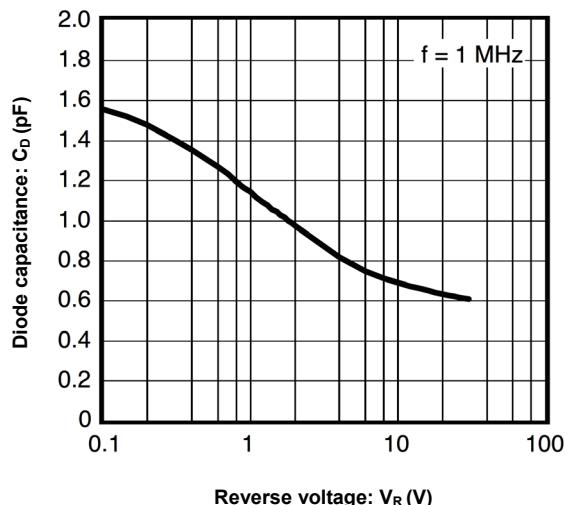
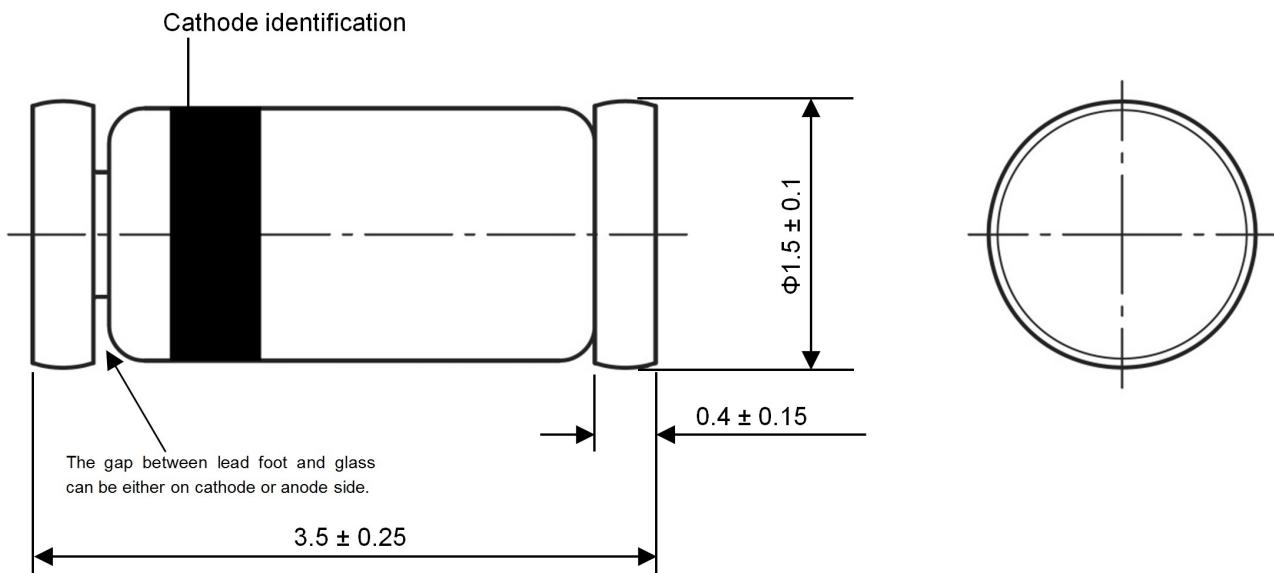


Figure 4. Diode capacitance vs. reverse voltage

Dimensions in mm



Glass Case

Mini Melf / SOD-80
JEDEC DO-213 AA

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